

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$ $T_C = +25^\circ C$
30V	12m $\Omega$ @ $V_{GS} = 10V$	37.8A
	16m $\Omega$ @ $V_{GS} = 4.5V$	32.8A

## Description

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

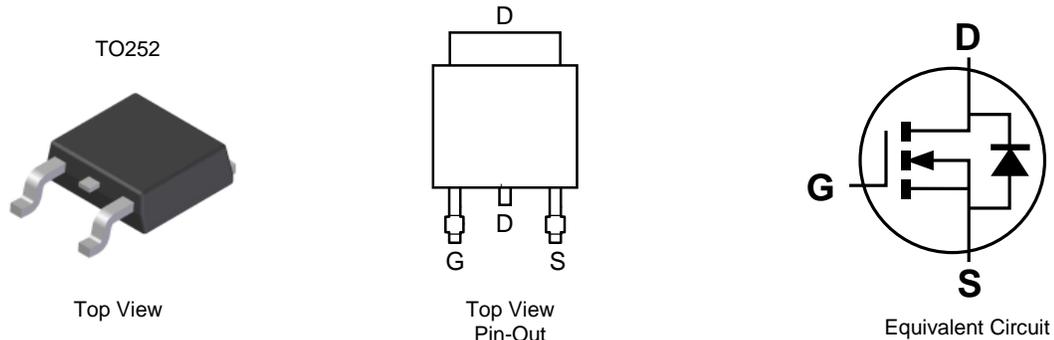
- Backlighting
- DC-DC Converters
- Power Management Functions

## Features

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Note 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.33 grams (Approximate)

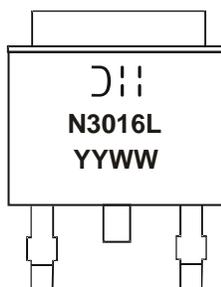


## Ordering Information (Notes 4)

Product	Case	Packaging
DMN3016LK3-13	TO252	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



 = Manufacturer's Marking  
 N3016L = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 14 = 2014)  
 WW = Week (01 - 53)

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	12.4 10	A
	Steady State	$T_C = +25^\circ\text{C}$ $T_C = +70^\circ\text{C}$	$I_D$	37.8 30.3	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	17 13.6	A
Maximum Body Diode Continuous Current			$I_S$	2	A
Pulsed Drain Current (10 $\mu\text{s}$ pulse, duty cycle = 1%)			$I_{DM}$	90	A
Avalanche Current (Note 7) $L = 0.1\text{mH}$			$I_{AS}$	22	A
Avalanche Energy (Note 7) $L = 0.1\text{mH}$			$E_{AS}$	24	mJ

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$		$P_D$	1.6	W
	$T_A = +70^\circ\text{C}$			1.0	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		$R_{\theta JA}$	75	$^\circ\text{C/W}$
	$t < 10\text{s}$			34	
Total Power Dissipation (Note 6)	$T_A = +25^\circ\text{C}$		$P_D$	2.8	W
	$T_A = +70^\circ\text{C}$			1.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		$R_{\theta JA}$	46	$^\circ\text{C/W}$
	$t < 10\text{s}$			24	
Thermal Resistance, Junction to Case (Note 6)			$R_{\theta JC}$	3.1	
Operating and Storage Temperature Range			$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 8)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 8)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.3	—	2.3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	8	12	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 11A
		—	12	16		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 9A
Diode Forward Voltage	V <sub>SD</sub>	—	0.70	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS</b> (Note 9)						
Input Capacitance	C <sub>iss</sub>	—	1415	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	119	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	82	—	pF	
Gate Resistance	R <sub>G</sub>	—	2.2	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	25.1	—	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 12A
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	11.3	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	3.5	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	3.6	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	—	4.8	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V, R <sub>L</sub> = 1.25Ω, R <sub>G</sub> = 3Ω,
Turn-On Rise Time	t <sub>r</sub>	—	16.5	—	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	26.1	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	5.6	—	ns	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	—	12.3	—	ns	I <sub>F</sub> = 12A, di/dt = 500A/μs
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	—	10.4	—	nC	

**NEW PRODUCT**

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - UIS in production with L = 0.1mH, starting T<sub>A</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

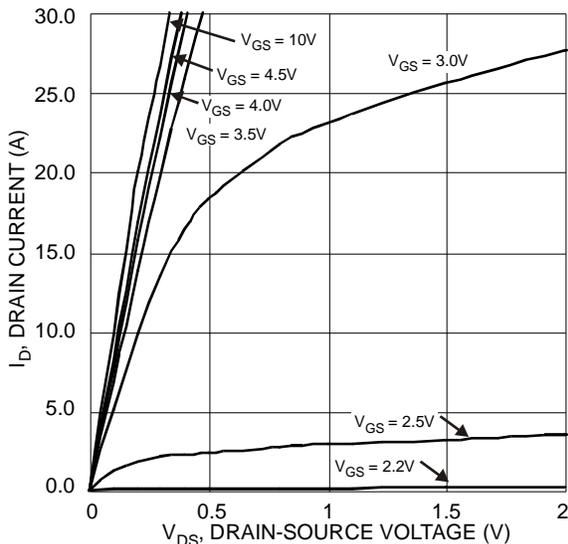


Figure 1 Typical Output Characteristic

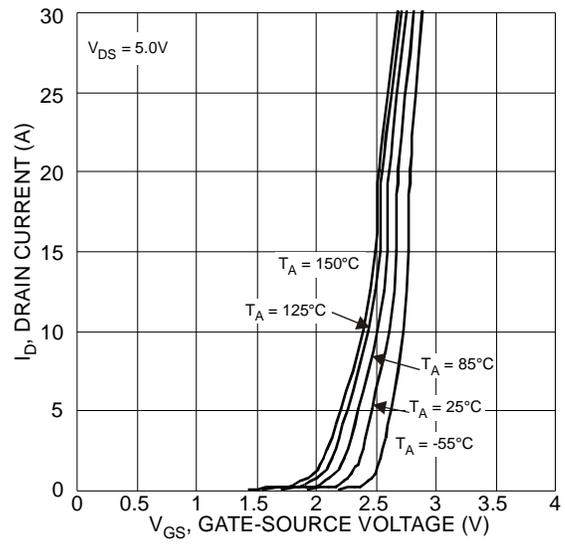


Figure 2 Typical Transfer Characteristics

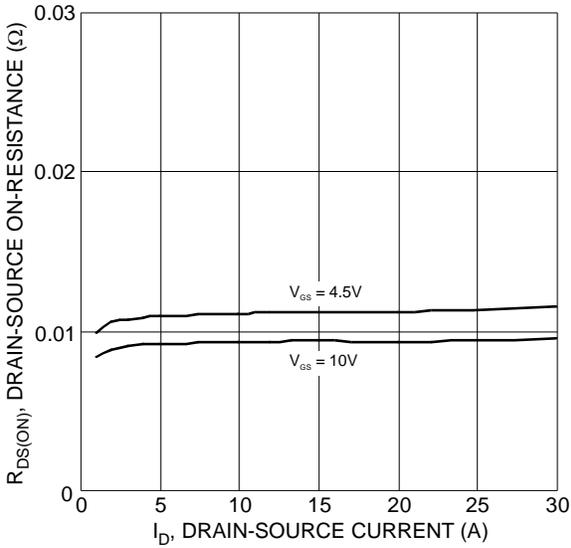


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

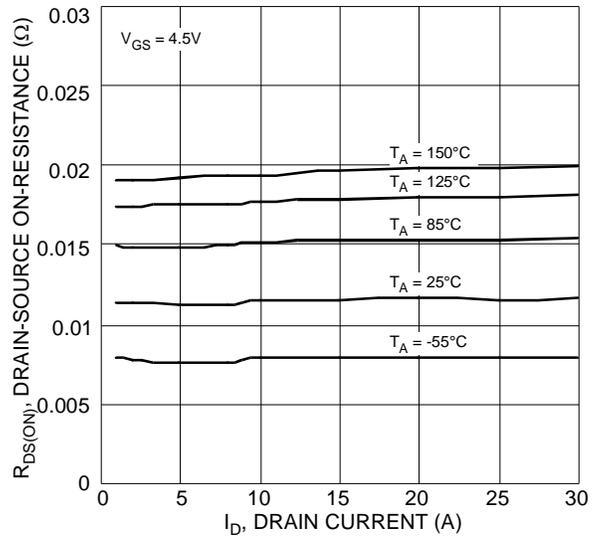


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

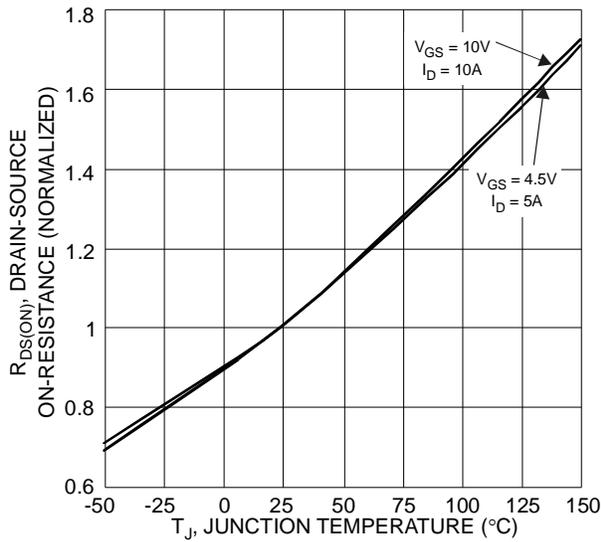


Figure 5 On-Resistance Variation with Temperature

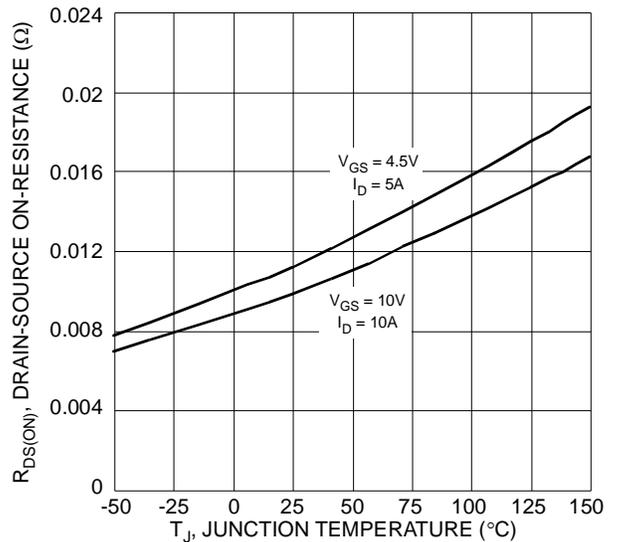


Figure 6 On-Resistance Variation with Temperature

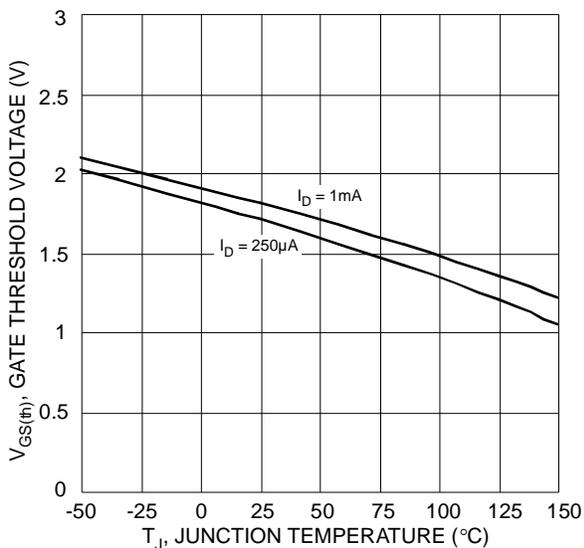


Figure 7 Gate Threshold Variation vs. Ambient Temperature

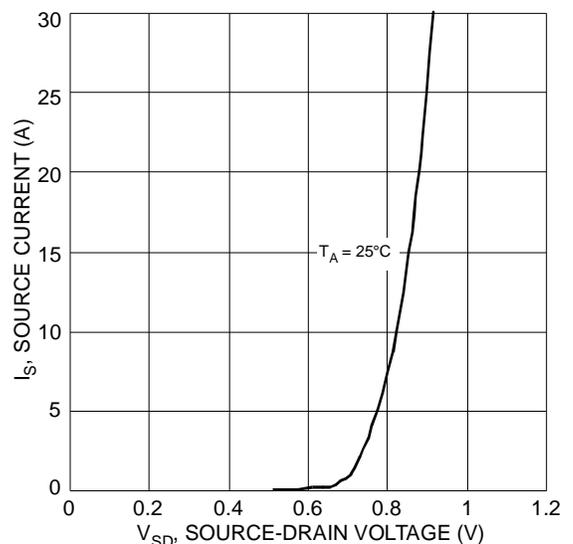


Figure 8 Diode Forward Voltage vs. Current

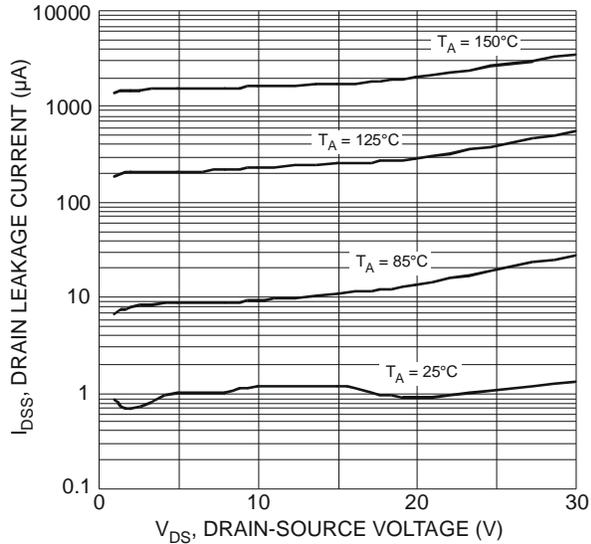


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

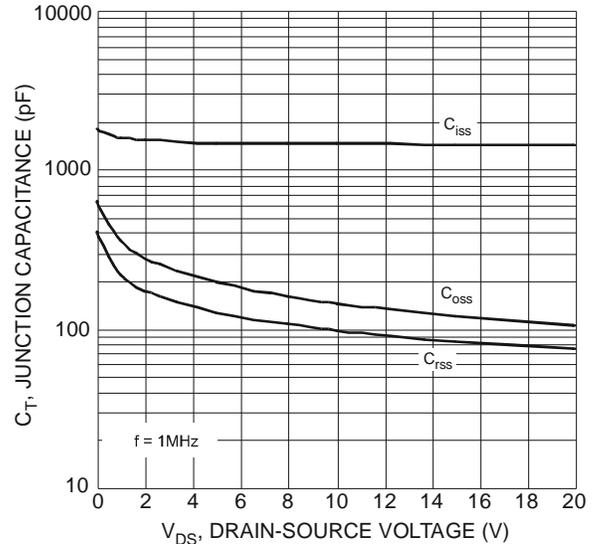


Figure 10 Typical Junction Capacitance

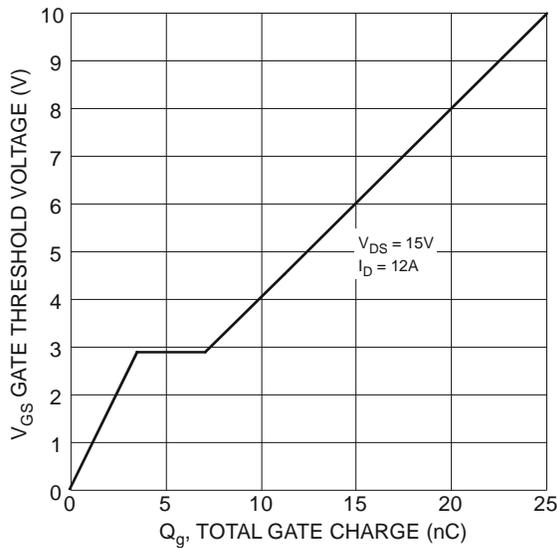


Figure 11 Gate Charge

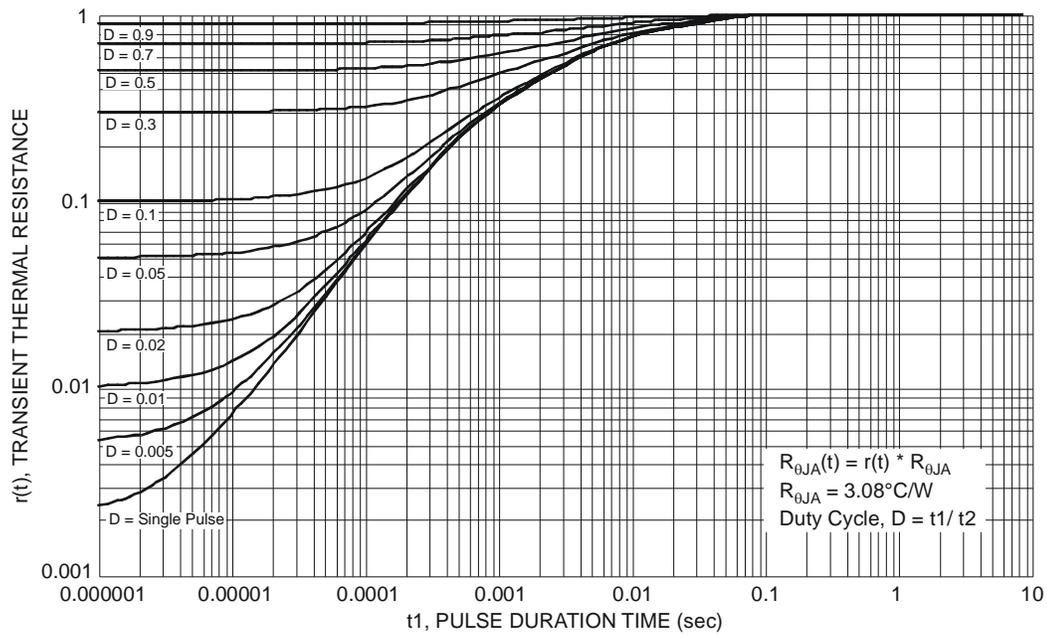
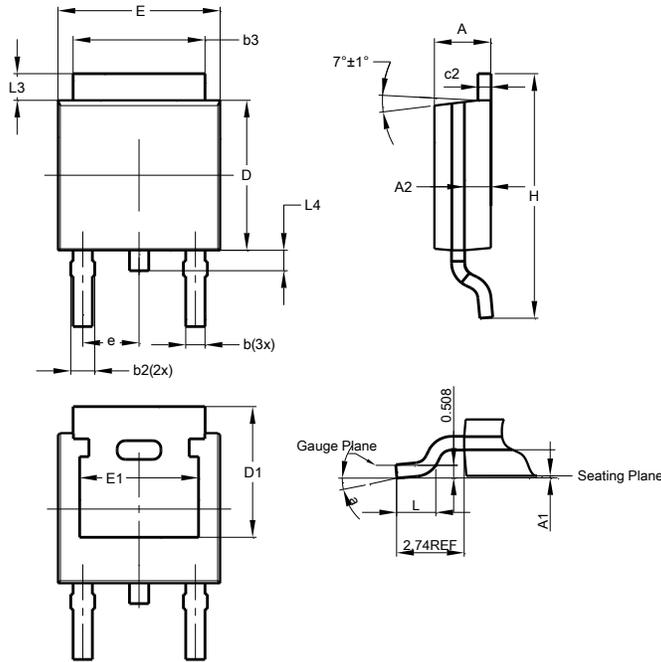


Figure 12 Transient Thermal Resistance

**Package Outline Dimensions**

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

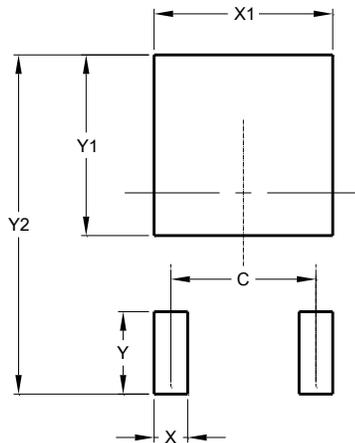


TO252			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	—	—
e	—	—	2.286
E	6.45	6.70	6.58
E1	4.32	—	—
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	—
All Dimensions in mm			

NEW PRODUCT

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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